

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Previously Presented) A semiconductor layer, comprising:
 - a first layer comprising a Ga_2O_3 system single crystal substrate; and
 - a second layer comprising a nitride surface of said first layer containing oxygen and nitrogen.
- 2-3. (Cancelled.)
4. (Previously Presented) A semiconductor layer according to claim 1, wherein the first layer comprises Ga_2O_3 , $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ where $0 \leq x < 1$, $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ where $0 \leq x < 1$, $(\text{In}_x\text{Al}_{1-x-y})_2\text{O}_3$ where $0 \leq x < 1$, $0 \leq y < 1$, and $0 \leq x + y < 1$ as a main constituent.
5. (Cancelled.)
6. (Currently Amended) A semiconductor layer, comprising:
 - a first layer comprising a Ga_2O_3 system ~~semiconductor~~ single crystal substrate;
 - a second layer comprising a nitride surface of said first layer containing oxygen and nitrogen; and
 - a third layer comprising a GaN system epitaxial layer grown on the second layer.
- 7-8. (Cancelled.)
9. (Previously Presented) A semiconductor layer according to claim 1, wherein the first layer consists of a single crystal $\beta\text{-}\text{Ga}_2\text{O}_3$.
10. (Previously Presented) A semiconductor layer according to claim 9, wherein the single crystal $\beta\text{-}\text{Ga}_2\text{O}_3$ has a prismatic shape having a square in cross section, and its axis direction matches a-axis <100> orientation, b-axis <010> orientation, or c-axis <001> orientation.

11. (Previously Presented) A semiconductor layer according to claim 1, wherein the first layer comprises $(In_xGa_{1-x})_2O_3$ where $0 < x < 1$.
12. (Previously Presented) A semiconductor layer according to claim 1, wherein the first layer comprises $(Al_xGa_{1-x})_2O_3$ where $0 < x < 1$.
13. (Previously Presented) A semiconductor layer according to claim 1, wherein the first layer comprises $(In_xAl_yGa_{1-x-y})_2O_3$ where $0 < x < 1$, $0 < y < 1$, and $0 < x + y < 1$.
14. (Cancelled.)
15. (Previously Presented) A semiconductor layer according to claim 6, wherein the first layer consists of single crystal β - Ga_2O_3 .
- 16-20. (Cancelled.)
21. (Previously Presented) A semiconductor layer, comprising:
 - a first layer comprising a Ga_2O_3 system single crystal substrate; and
 - a second layer comprising a nitride surface of said first layer which contains oxygen and nitrogen,wherein the second layer comprises a GaN system compound semiconductor.